

IN THE SPECIFICATION

Please amend the specification as follows:

Page 1, paragraph 1:

BACKGROUND AND SUMMARY OF THE INVENTION

The invention relates to a method of manufacturing a semiconductor device, wherein a semiconductor body is provided, at a surface, with an isolation region which is recessed in the semiconductor body, which isolation region defines a continuous active region in the semiconductor body wherein a transistor having, adjacent to the surface, emitter and collector regions of a first conductivity type and a base region of the opposite, second conductivity type are formed, said emitter, base and collector regions each being provided with a contact region, for which purpose a first silicon layer is deposited on the surface, from which silicon layer two of said three contact regions are formed, which are mutually separated by an intermediate region wherein the first semiconductor layer is removed, which intermediate region extends transversely over the length of the active region, whereafter a second silicon layer is deposited, which is electrically insulated from the first silicon layer, and from which second silicon layer the third contact region is formed at the location of the intermediate region between the two contact regions mentioned first. Such a method is disclosed, inter alia, in the patent document US-A 5,204,274.

Page 3, paragraph 3:

BRIEF DESCRIPTION OF THE DRAWING

In the drawings:

Page 3, paragraph 11:

DETAILED DESCRIPTION OF THE INVENTION

It is to be noted that the drawings are diagrammatic and not to scale. Fig. 2a, 3a, 4a and 5a are sectional views taken on the line A-A; Fig. 2b, 3b, 4b and 5b are sectional views of the device taken on the line B-B in Fig. 1.